



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.: 10/632,186 Filing Date: July 30, 2003
Confirmation No.: 3961
First Named Inventor: Yi Ding
Assignee: ProMOS Technologies, Inc.
Examiner: Nguyen, Thanh T. Art Unit: 2813
Attorney Docket No.: M-15241 US

San Jose, California
October 12, 2004

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
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INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR § 1.97(C)

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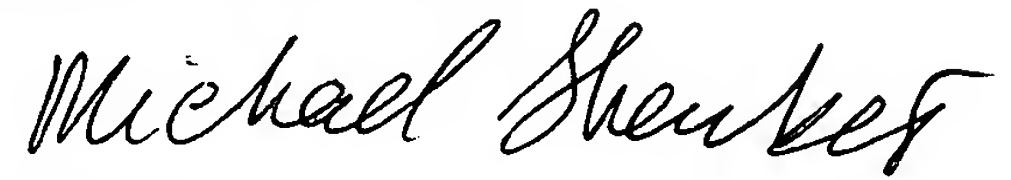
Application No. 10/632,186

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Respectfully submitted,



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| U.S. Department of Commerce, Patent and Trademark Office | | Atty Docket No. | Serial No. |
| | | M-15241 US | 10/632,186 |
| INFORMATION DISCLOSURE STATEMENT BY APPLICANT | | Applicant(s) | |
| (Use several sheets if necessary) | | Yi Ding | |
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